ABSTRACT OF THE DISCLOSURE

CHEMICAL MECHANICAL POLISH (CMP) ENDPOINT DETECTION BY COLORIMETRY

A method for fabricating a microelectronics fabrication. There is first provided a substrate employed within a microelectronics fabrication. There is then formed over the substrate a planarizable layer. The planarizable layer has a lower residual portion of the planarizable layer and an upper removable portion of the planarizable layer, where one of the lower residual portion of the planarizable layer and the upper removable portion of the planarizable layer has a colorant incorporated therein. The colorant is positioned at a location which assists in monitoring and controlling an endpoint of a chemical mechanical polish (CMP) planarizing method employed in planarizing the planarizable layer. There is then planarized through the chemical mechanical polish (CMP) planarizing method the planarizable layer while employing the colorant concentration to determine the endpoint of the chemical mechanical polish (CMP) planarizing method.

FIGURE 1 IS SUGGESTED FOR PUBLICATION